

Fifty shades of TiN:

How deposition conditions influence growth morphology and structure, and thereby hardness and especially fracture toughness

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The outstanding properties and property-combinations of transition metal nitrides (TMNs) - such as high strength, good wear resistance, high temperature stability, combined with chemical resistance – lend them their wide range of applications spanning from structural to protective to functional materials. These include protective coatings for machining tools, or corrosion- and abrasion-resistant coatings for applications in the aerospace and automotive industries. In addition, TMNs are used as diffusion barriers, for example in microelectronics, or simply as decorative coatings (especially TiN). For many investigations and characterizations, TiN is a welcome benchmark. Here, about fifty different TiN coatings were prepared by reactive as well as non-reactive magnetron sputtering — and investigated for their microstructure and mechanical properties.

Deposition parameter variations (for ~50 different TiN's)

- substrate-to-target distance **ST: 4 x** (40 130 mm)
- deposition pressure \mathbf{p}_t : 2 x (0.4 and 0.7 Pa)
- bias potential **U**_b: **5** x (-20, -40, -50, -60, -80 V)
- substrate temperature T_s : 7 x (150 700 °C)
- N_2 gas volume fraction F_{N2} : 5 x (0, 12.5, 30, 45, 70 %)
- sputtering power density **P_m: 5 x** (3, 7.5, 9, 11, 13 W/cm²)
- targets: → BIAS (and heating) 2 x (Ti and TiN)

• substrates: Si(100),

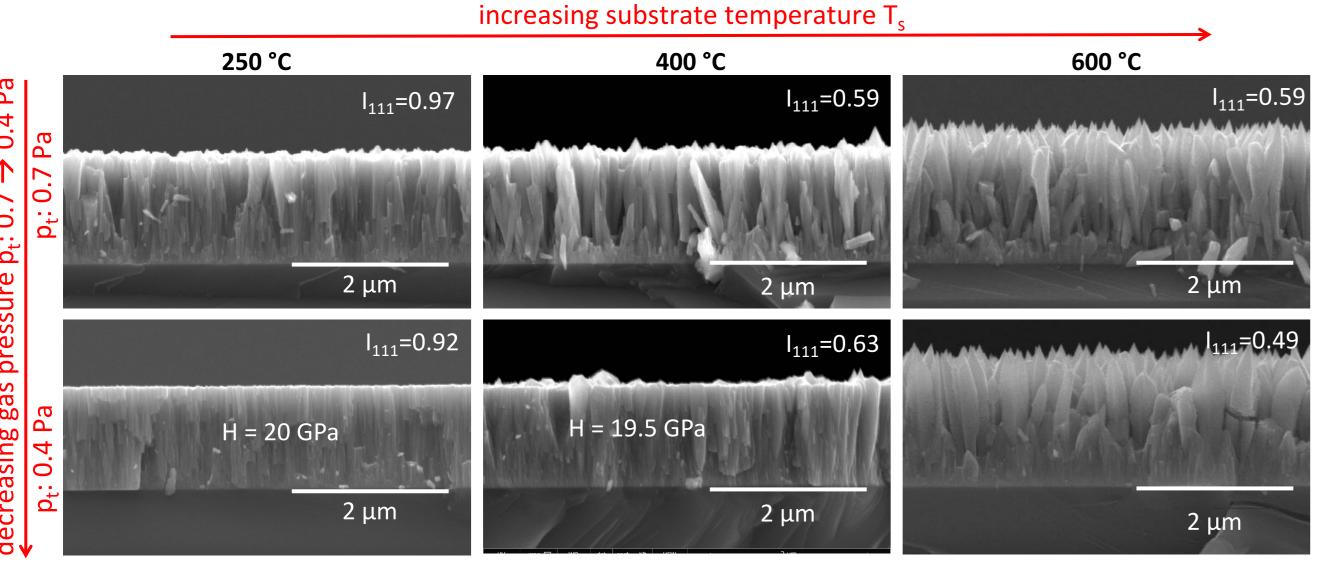
MgO(100)-(110)-(111) Al_2O_3 , austenite

Mass spectroscopy measurements

during reactive (Ti-target) or non-reactive (TiN-target) magnetron sputtering of TiN $(P_m: ^7.5 \text{ W/cm}^2)$ [1].

non-reactive: ~10x higher Ti⁺ and Ti²⁺ • ~10²x lower N^+ and N_2^+ $no N_2$ \blacksquare Ar⁺ \blacksquare Ar²⁺ TiN-0% Ti-0% Ti-17% Ti-45%

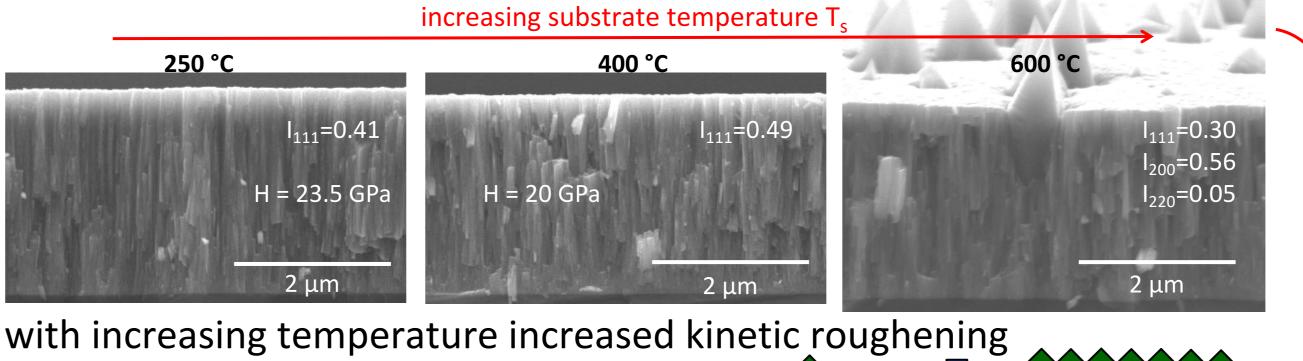
Non-reactive deposition (U_b = -40 V, P_m = 7.5 W/cm²)



decreasing gas pressure p_t : 0.7 \rightarrow 0.4 Pa (fewer collisions \Rightarrow higher energy of film forming species)

column tops are faceted due to kinetic roughening

• Non-reactive deposition ($p_t = 0.4 Pa$, $U_b = -40 V$, $P_m = 13 W/cm^2$)



lower adatom potential

energy on (111)

111

PUMPING

substrate For low temperature: Polar 111-surfaces (with three backbonds) result in a higher adatom incorporation

probability on 111-grains, which finally over-grow the non-polar 002-grains.

-80 V H = 30 GPa 111 002 2 μm

 $T_s = 600 \, ^{\circ}C$

low ion density: (220) for E_i: 60–90 eV in agreement with earlier studies [2]) P.H. Mayrhofer, M. Geier, C. Löcker, L. Chen, Int. J. Mat. Res. (2009)

stress and lower stored

energy for (111) than (002).

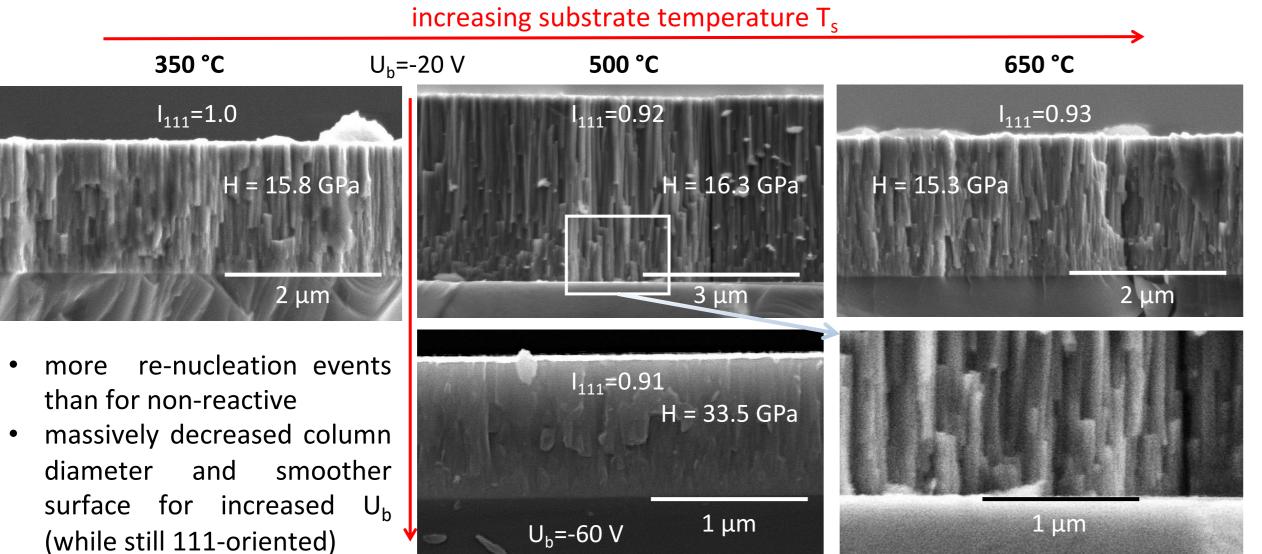
I₁₁₁=0.05

I₂₀₀=0.38

I₂₂₀=0.57

 $2 \mu m$

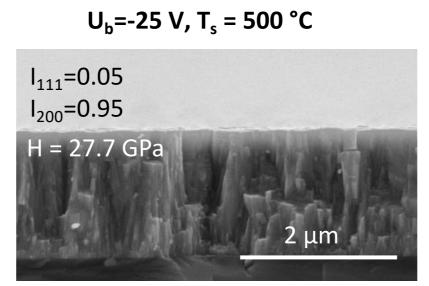
Reactive deposition ($p_t = 0.4 \text{ Pa}$, $F_{N2} = 30 \%$, ST = 11 cm, $P_m = 11 \text{ W/cm}^2$) •



increasing bias potential column tops are faceted, when U_b is low reduced substrate-target distance (ST = 4 cm)

increased sputtering power P_m : 7.5 \rightarrow 13 W/cm² (higher energy of film-forming species)

002-grains grow faster laterally



With increased plasma density, even at low dep. temperatures $(T_s = 150 \, ^{\circ}C)$, dense growth morphologies are possible, and high hardness. Rule of thumb for 1 collision:

 $p(Pa)\cdot\Lambda(cm)\approx 1$ Thus, the mean free path Λ at 0.4 Pa is 2.5 cm.

H ≤ 20 GPa for:

bias potential U_b (V)

open columnar growth

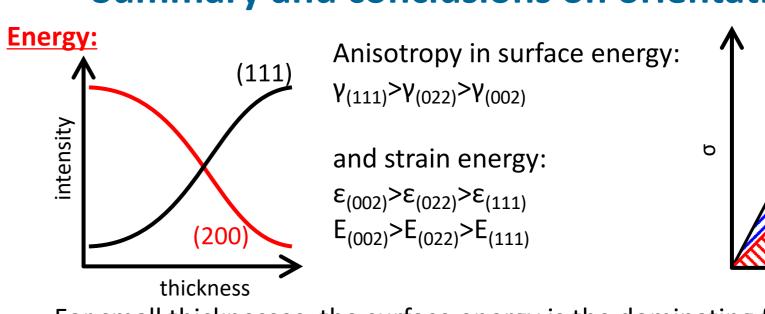
H = 19.5 GPa

2 µm

I₁₁₁=0.63

I₁₁₁=0.93

Summary and conclusions on orientation changes For the same strain, lower



Probably overrated as easily overruled by other energetic and kinetic effects.

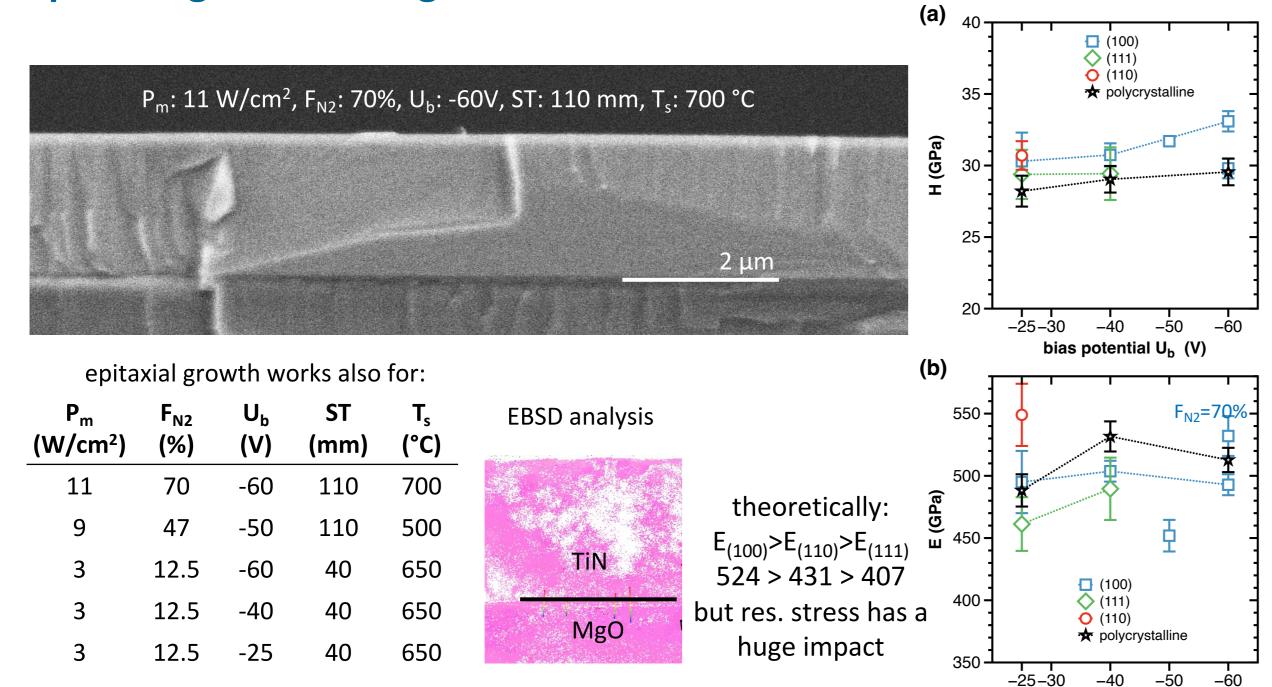
For small thicknesses, the surface energy is the dominating factor. \Rightarrow (200)-orientation for TiN, as the (200)-surface has the lowest energy! With increasing thickness the (111) will be preferred.

Energy and kinetics: (111) wins (at low T) by overgrowing (200), due to the higher adatom incorporation (lower adatom potential energy at 111). At higher T, (200) is preferred, but depends thickness on sputter conditions. N₂⁺ irradiation

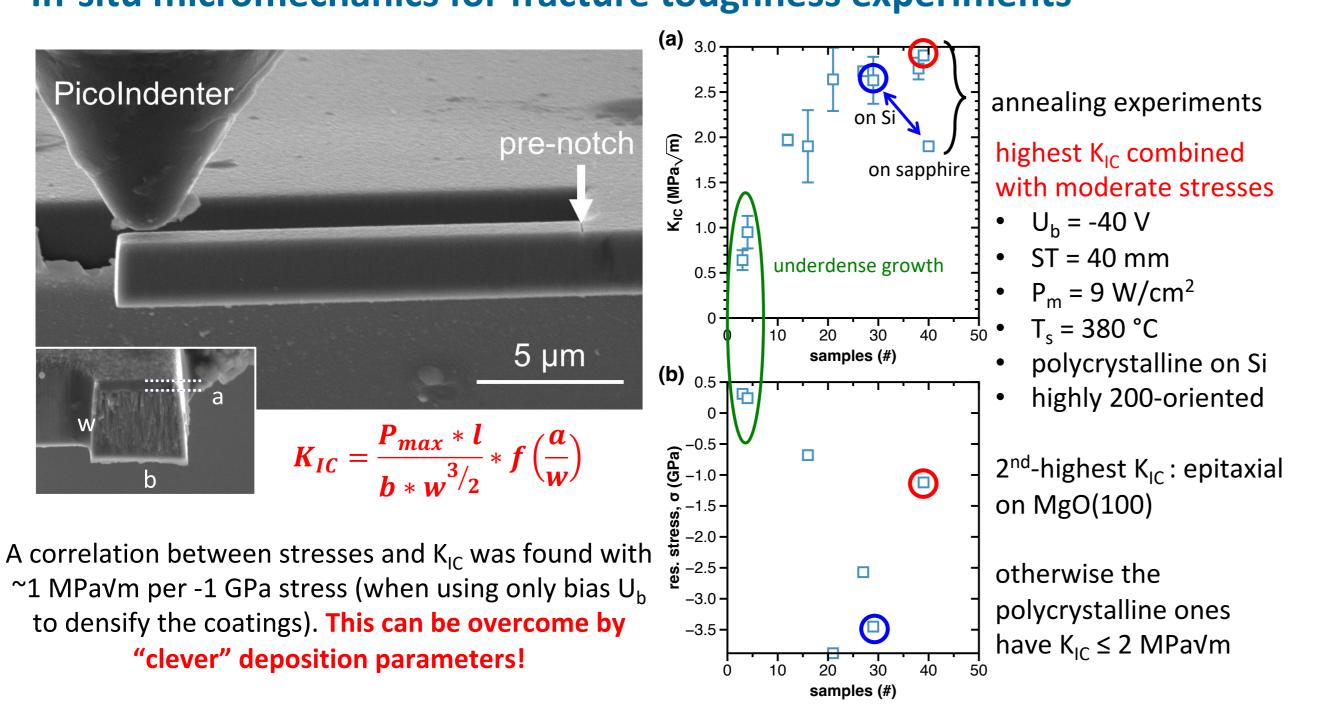
Ò-----O

The (002) columns win by overgrowing the (111) columns for high N₂⁺ irradiation! N chemisorbs easier on (001) than on (111). (Difficult for nonreactive, as lower N₂⁺)

Epitaxial growth on MgO



In-situ micromechanics for fracture toughness experiments



orientation $H = 15.3 \, GPa$ σ↑⇒Ε↑ (100) (111) (110) theoretically: $E_{(002)} > E_{(022)} > E_{(111)}$ 2 µm

≥ 30 **GPa** for:

MgO(100) &

MgO(110)

high bias (large ST) ਫ਼ੁੰ

epitaxial growth on g

indentation modulus: (b) 1.0 —

better correlates with

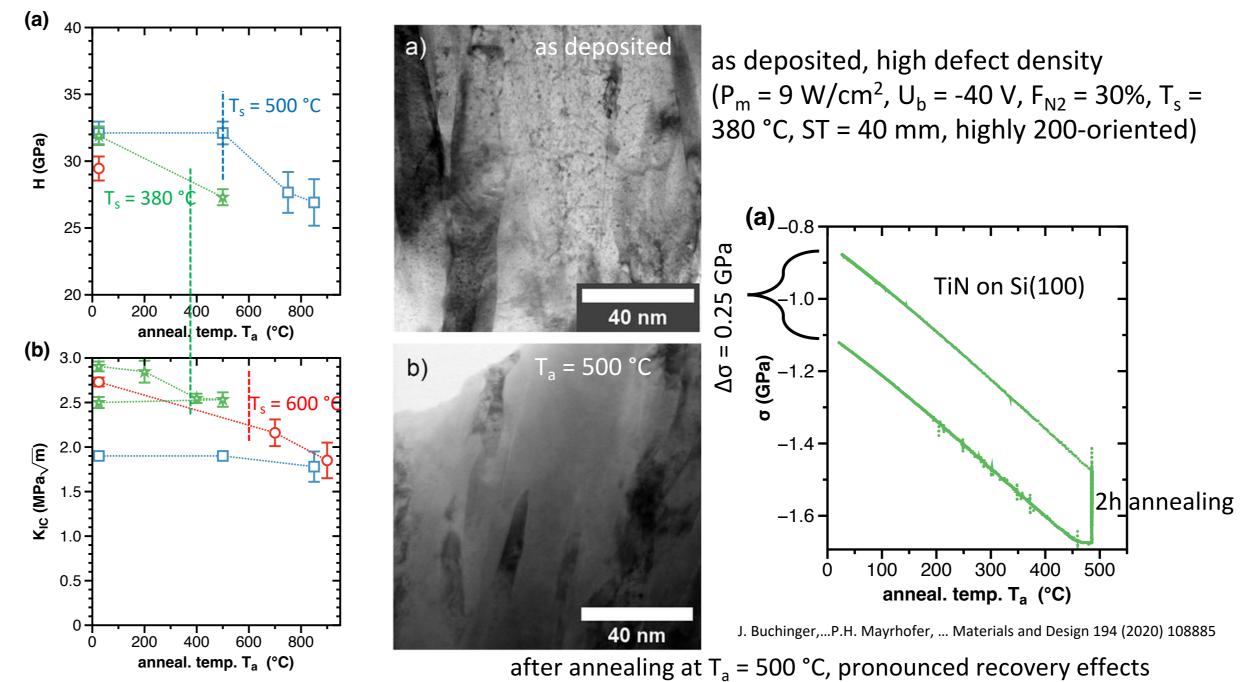
residual stresses than

low bias (small ST)

Overview on indentation hardness and residual stresses

samples (#)

Annealing experiments of selected TiN coatings



J. Buchinger, L. Löfler, J. Ast, A. Wagner, Z. Chen, J. Michler, Z.L. Zhang, P.H. Mayrhofer, D. Holec, M. Bartosik, Materials and Design 194 (2020) 108885

4. Conclusions

- Plasma conditions are extremely important for proper coating development and reproducibility.
- Low ion energies but high intensity is preferred.
- Rougher films for nonreactive deposition when using similar P_m, T_s, U_b, ST
- Densification obtained by high energy (≥ 80 eV) ion bombardment comes at a steep price: Significant Lattice defects; Compressive stresses; Discharge gas incorporation
- > The plasma influences, morphology, chemistry, structure and hence material properties.
- \triangleright Highest *H* (32 GPa) and K_{IC} (2.9 MPavm) combination for 200-oriented film, obtained by low U_b and intense plasma.